

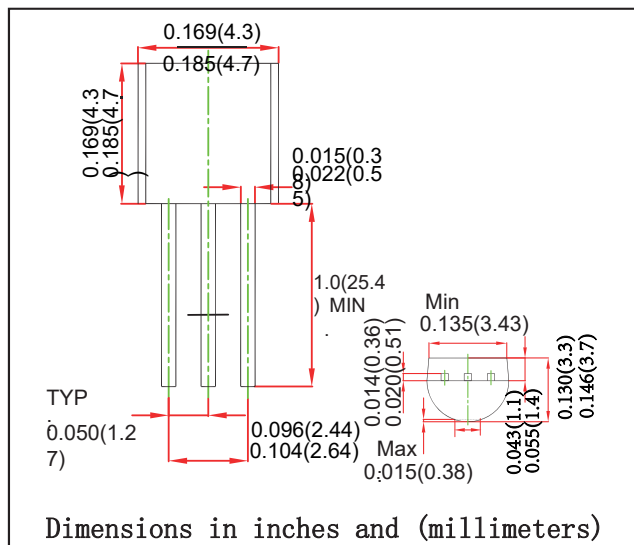
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Switching and amplification in high voltage
- Applications such as telephony
- Low current
- High voltage
- NPN Transistors

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current-continuous	I_C	0.6	A
Collector Power Dissipation	P_C	625	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	200	°C / W
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.01mA, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10mA, I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB} = 500V, I_E = 0$			0.01	uA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4.0V, I_C = 0$			0.1	uA
DC current gain	h_{FE}	$I_C = 1.0mA, V_{CE} = 10V$	100		300	
		$I_C = 0.1mA, V_{CE} = 10V$	35			
		$I_C = 500mA, V_{CE} = 10V$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1.0	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$			2.0	V
		$I_C = 50mA, I_B = 5mA$			1.0	
Transistor frequency	f_T	$V_{CE} = 20V, I_C = 20mA, f = 100MHz$	250			MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 100MHz$			8	pF
Delay time	T_d	$V_{CC} = 30V, V_{BE} = -0.5V$			10	ns
Rise time	T_r	$I_C = 150mA, I_{B1} = 15mA$			25	ns
Storage time	T_s	$V_{CC} = 30V, I_C = 150mA$			225	ns
Fall time	T_f	$I_{B1} = I_{B2} = 15mA$			60	ns

* Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$.

RATINGS AND CHARACTERISTIC CURVES

